

In the Claims:

Please amend claims 3, 5 and 13, and cancel claims 1-2, 4, 6-12 and 14-16 as indicated below. This listing of claims replaces all prior versions.

1. (Canceled)

2. (Canceled)

3. (Currently Amended) ~~Method according to claim 2, for manufacturing a floating gate~~
type semiconductor device on a substrate having a surface, the method comprising:

forming, on the substrate surface, a stack comprising an insulating film, a first layer of floating gate material and a layer of sacrificial material,

forming at least one isolation zone through the stack and into the substrate, the first layer of floating gate material thereby having a top surface and side walls,

removing the sacrificial material, thus leaving a cavity defined by the isolation zones and the top surface of the first layer of floating gate material, and

filling the cavity with a the second layer of floating gate material having side walls, the first layer of floating gate material and the second layer of floating gate material thus forming together a floating-gate,

wherein the isolation zones are removed so as to completely expose the side walls of the second layer of floating gate material and part of the side walls of the first layer of floating gate material.

4. (Canceled)

5. (Currently Amended) ~~Method according to claim 1, furthermore comprising the step of for manufacturing a floating gate type semiconductor device on a substrate having a~~
surface, the method comprising:

forming, on the substrate surface, a stack comprising an insulating film, a first layer of floating gate material and a layer of sacrificial material,

forming at least one isolation zone through the stack and into the substrate, the first layer of floating gate material thereby having a top surface and side walls,

removing the sacrificial material, thus leaving a cavity defined by the isolation zones and the top surface of the first layer of floating gate material,

filling the cavity with a second layer of floating gate material, the first layer of floating gate material and the second layer of floating gate material thus forming together a floating-gate, and

forming a protection layer between the first layer of floating gate material and the sacrificial layer.

6. (Canceled)

7. (Canceled)

8. (Canceled)

9. (Canceled)

10. (Canceled)

11. (Canceled)

12. (Canceled)

13. (Currently Amended) Method according to claim 11, further comprising for manufacturing a floating gate type semiconductor device on a substrate having a surface, the method comprising:

forming, on the substrate surface, a stack comprising an insulating film, a first layer of floating gate material and a layer of sacrificial material,

forming at least one isolation zone through the stack and into the substrate, the first layer of floating gate material thereby having a top surface and side walls,

removing the sacrificial material, thus leaving a cavity defined by the isolation zones and the top surface of the first layer of floating gate material.

filling the cavity with a second layer of floating gate material having sidewalls, the first layer of floating gate material and the second layer of floating gate material thus forming together a floating-gate,

partially removing the isolation zones so as to completely expose the side walls of the second layer of floating gate material and to partially expose the side walls of the first layer of floating gate material, and

forming a protection layer between the first layer of floating gate material and the sacrificial layer.

14. (Canceled)

15. (Canceled)

16. (Canceled)